

Small Signal MOSFET

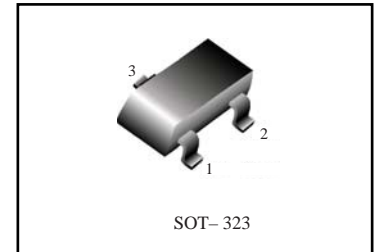
25 V, 0.75 A, Single, N-Channel, ESD Protection, SC-70/SOT-323

Features

- Advance Planar Technology for Fast Switching, Low $R_{DS(on)}$
- Higher Efficiency Extending Battery Life
- This is a Pb-Free Device

Applications

- Boost and Buck Converter
- Load Switch
- Battery Protection



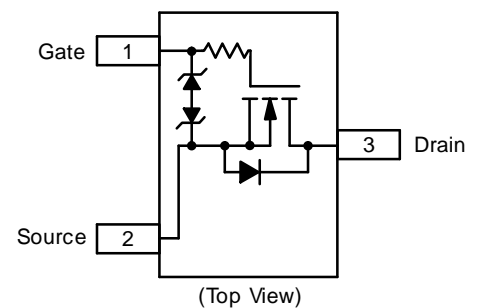
MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	25	V
Gate-to-Source Voltage			V_{GS}	± 8.0	V
Drain Current	$t < 5\text{ s}$	$T_A = 25^\circ\text{C}$	I_D	0.75	A
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	I_D	0.7	A
		$T_A = 75^\circ\text{C}$		0.6	
Power Dissipation (Note 1)	Steady State		P_D	0.28	W
Power Dissipation (Note 1)	$t \leq 5\text{ s}$		P_D	0.33	W
Pulsed Drain Current	$t_p = 10\ \mu\text{s}$		I_{DM}	3.0	A
Operating Junction and Storage Temperature			T_J, T_{STG}	-55 to +150	$^\circ\text{C}$
Source Current (Body Diode) (Note 1)			I_S	0.3	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^\circ\text{C}$
ESD Rating – Machine Model				250	V

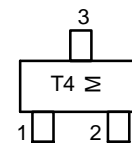
$V_{(BR)DSS}$	$R_{DS(on)}$ Typ	I_D Max
25 V	249 m Ω @ 4.5 V	0.75 A
	299 m Ω @ 2.7 V	

PIN CONNECTIONS

SOT-323 (3- Leads)



MARKING DIAGRAM



T4 = Specific Device Code
M = Month Code

THERMAL RESISTANCE RATINGS

Rating	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	450	$^\circ\text{C/W}$
Junction-to-Ambient – $t \leq 5\text{ s}$ (Note 1)	$R_{\theta JA}$	375	

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

Device	Package	Shipping
FTK4409	SOT-323 (Pb-Free)	3000/Tape & Reel



ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
----------------	--------	----------------	-----	-----	-----	------

OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	25			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			30		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 20 V	T _J = 25°C		0.5	μA
			T _J = 70°C		2.0	
			T _J = 125°C		5.0	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = 8.0 V			3	uA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	0.65		1.5	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J			-2.0		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 0.6 A		249	350	mΩ
		V _{GS} = 2.7 V, I _D = 0.2 A		299	400	
		V _{GS} = 4.5 V, I _D = 1.2 A		260		
Forward Transconductance	g _{FS}	V _{DS} = 5.0 V, I _D = 0.5 A		0.5		S

CHARGES AND CAPACITANCES

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 10 V		49	60	pF
Output Capacitance	C _{OSS}			22.4	30	
Reverse Transfer Capacitance	C _{RSS}			8.0	12	
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 15 V, I _D = 0.8 A		1.2	1.5	nC
Threshold Gate Charge	Q _{G(TH)}			0.2		
Gate-to-Source Charge	Q _{GS}			0.28	0.50	
Gate-to-Drain Charge	Q _{GD}			0.3	0.40	

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 4.5 V, V _{DS} = 15 V, I _D = 0.7 A, R _G = 51 Ω		5.0	12	ns
Rise Time	t _r			8.2	8.0	
Turn-Off Delay Time	t _{d(OFF)}			23	35	
Fall Time	t _f			41	60	

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 0.6 A	T _J = 25°C		0.82	1.20	V
-----------------------	-----------------	--	-----------------------	--	------	------	---

- Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

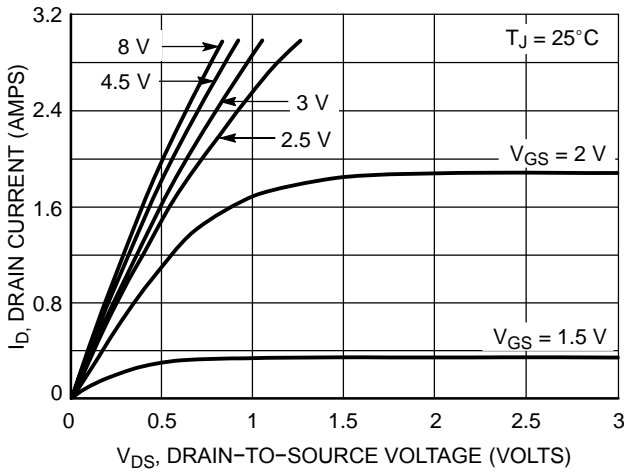


Figure 1. On-Region Characteristics

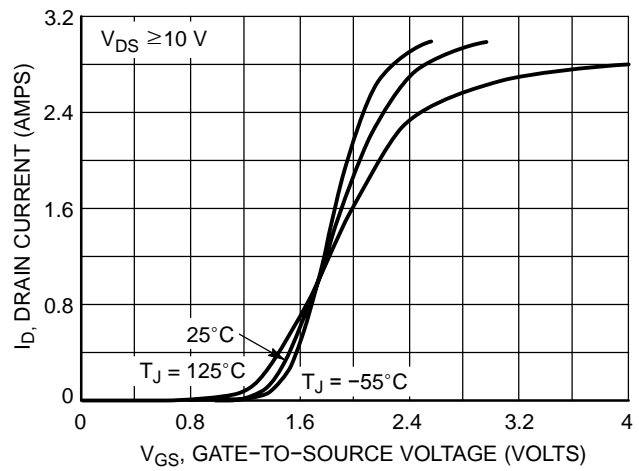


Figure 2. Transfer Characteristics

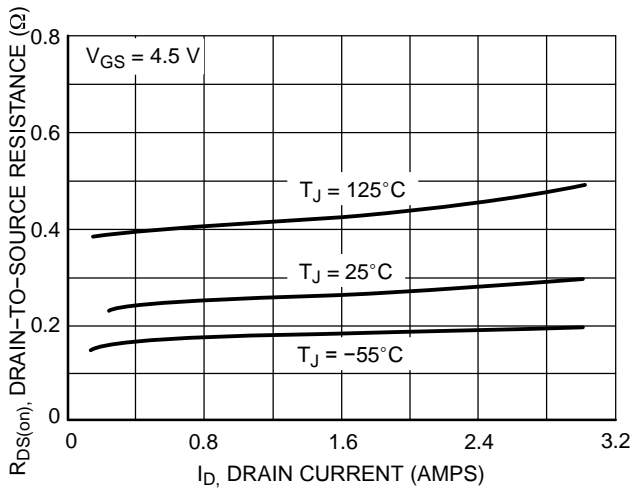


Figure 3. On-Resistance vs. Drain Current and Temperature

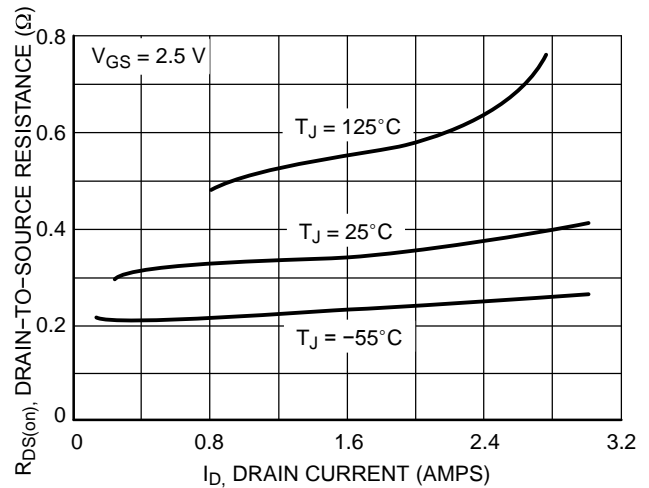


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

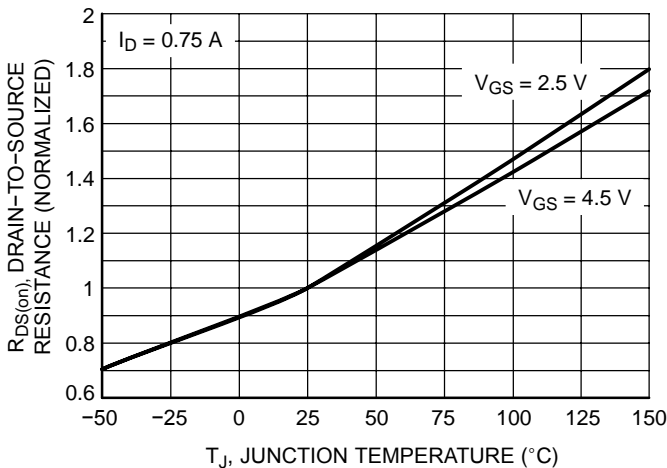


Figure 5. On-Resistance Variation with Temperature

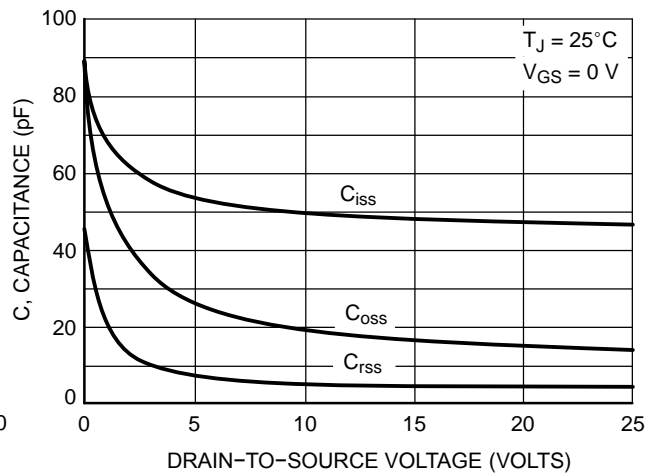


Figure 6. Capacitance Variation

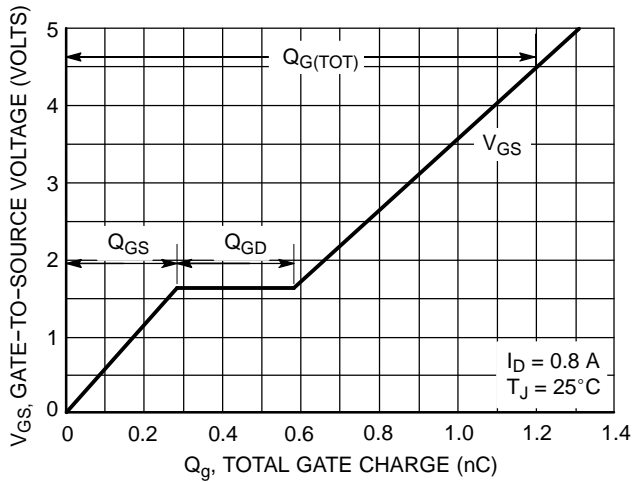


Figure 7. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

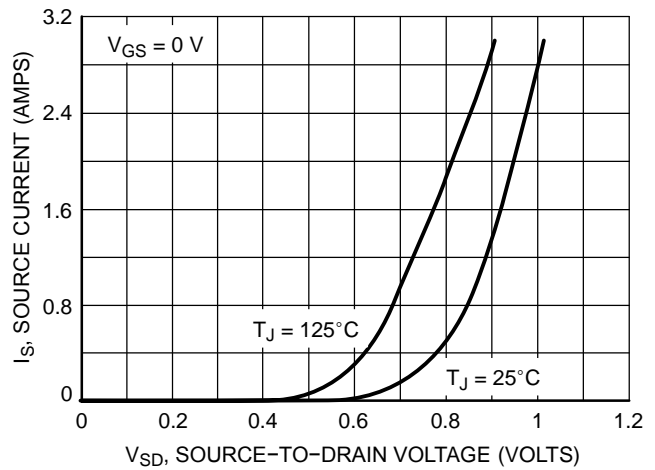
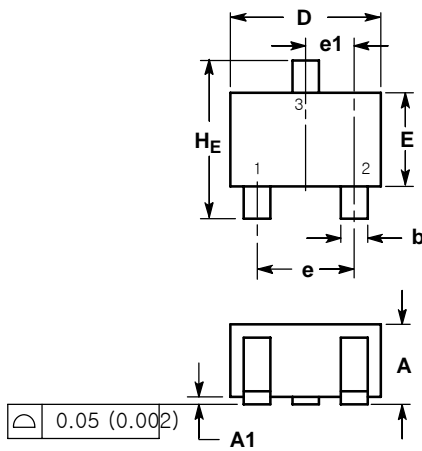


Figure 8. Diode Forward Voltage vs. Current

PACKAGE DIMENSIONS

SC-70 (SOT-323)



NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.7 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.425 REF			0.017 REF		
H _E	2.00	2.10	2.40	0.079	0.083	0.095

STYLE 8:
 PIN 1. GATE
 2. SOURCE
 3. DRAIN

SOLDERING FOOTPRINT*

